

ABSTRACT

A semiconductor device including a storage node and a method of fabricating the same is provided. In the method of fabricating the semiconductor device, an insulation layer is formed over a substrate, and a first hole and a second hole that penetrate the insulation layer are formed. A recess is formed in the insulation layer to overlap the first hole. A first conductive pattern that fills the first hole and the recess and a second conductive pattern that fills the second hole are formed. A third conductive pattern connected to the second conductive pattern is formed.

FIG. 20